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# BSH111BK

# 55 V, N-channel Trench MOSFET

26 November 2014

**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 3 kV HBM

### 3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	55	V
$V_{GS}$	gate-source voltage			-10	-	10	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	210	mA
		V <sub>GS</sub> = 4.5 V; T <sub>sp</sub> = 25 °C		-	-	335	mA
Static charac	teristics			'	'		,
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_D$ = 200 mA; $T_j$ = 25 °C		-	2.3	4	Ω

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.





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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S 017aaa255

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BSH111BK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
BSH111BK	%4T

[1] % = placeholder for manufacturing site code

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### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	55	V
V <sub>GS</sub>	gate-source voltage			-10	10	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	210	mA
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	130	mA
		V <sub>GS</sub> = 4.5 V; T <sub>sp</sub> = 25 °C		-	335	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	0.85	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	302	mW
			[1]	-	364	mW
		T <sub>sp</sub> = 25 °C		-	1449	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain o	liode		1	1		
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	200	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

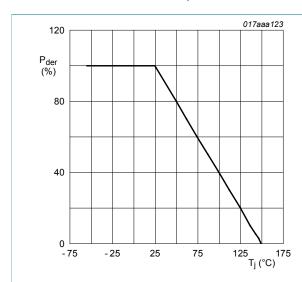


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

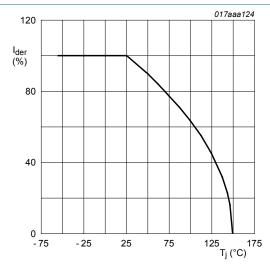


Fig. 2. Normalized continuous drain current as a function of junction temperature

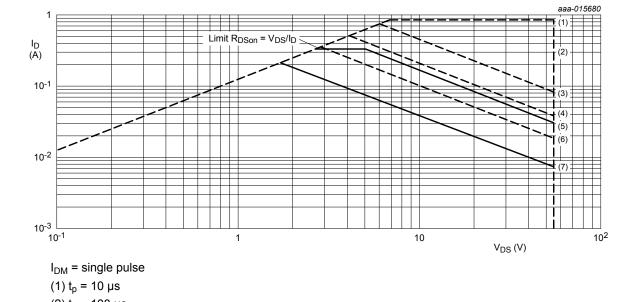
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100~\%$$

BSH111BK

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(2)  $t_p = 100 \ \mu s$ 

(3)  $t_p = 1 \text{ ms}$ 

(4)  $t_p = 10 \text{ ms}$ 

(5) DC;  $T_{sp}$  = 25 °C

(6)  $t_p = 100 \text{ ms}$ 

(7) DC;  $T_{amb}$  = 25 °C; drain mounting pad 1 cm<sup>2</sup>

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	351	404	K/W
			[2]	-	271	311	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

#### 55 V, N-channel Trench MOSFET

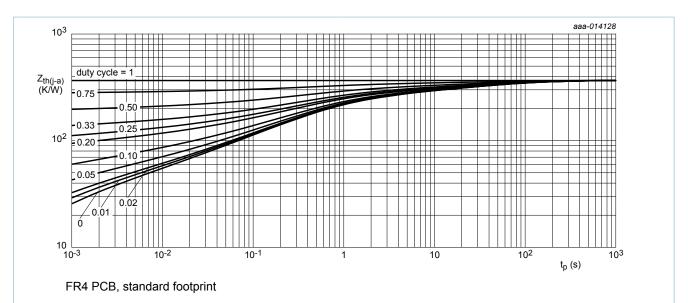
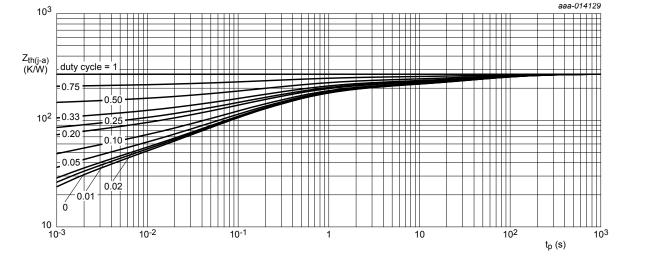


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		1			
$V_{(BR)DSS}$	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	55	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.6	1	1.3	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.3	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.3	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2.3	4	Ω
resistance	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C	-	4.7	8.1	Ω
		$V_{GS}$ = 2.5 V; $I_D$ = 75 mA; $T_j$ = 25 °C	-	2.7	5	Ω
		$V_{GS}$ = 1.8 V; $I_D$ = 30 mA; $T_j$ = 25 °C	-	4.8	-	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C	-	0.64	-	S
Dynamic ch	aracteristics		,			,
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 4.5 V;	-	0.5	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.08	-	nC
$Q_{GD}$	gate-drain charge		-	0.16	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	19.1	30	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	2.7	10	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.5	7	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $I_{D}$ = 200 mA; $V_{GS}$ = 4.5 V;	-	8.3	12	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	8.4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	12.6	16	ns
t <sub>f</sub>	fall time		-	4.8	-	ns
Source-drai	in diode	1	1		1	
V <sub>SD</sub>	source-drain voltage	$I_S$ = 200 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.86	1.2	V
		-				

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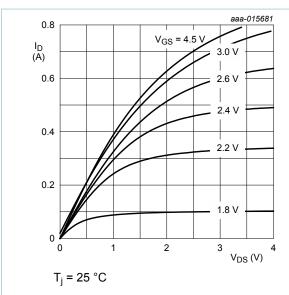
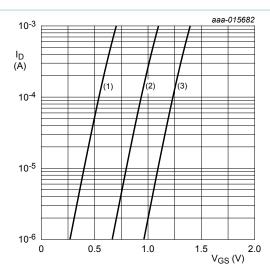


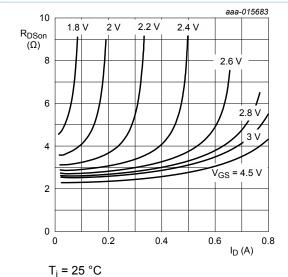
Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i$  = 25 °C;  $V_{DS}$  = 5 V

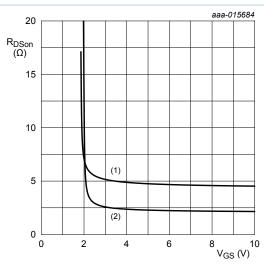
- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



of drain current; typical values

Fig. 8. Drain-source on-state resistance as a function



 $I_D = 0.2 A$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

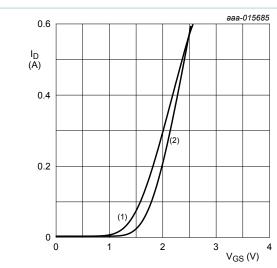
(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

2.5

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 $V_{DS} > I_D \times R_{DSon}$ (1)  $T_i = 25 \, ^{\circ}C$ 

(2)  $T_i = 150 \, ^{\circ}\text{C}$ 

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

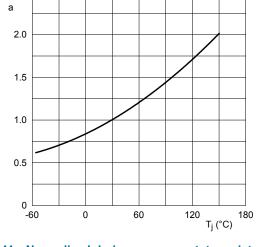
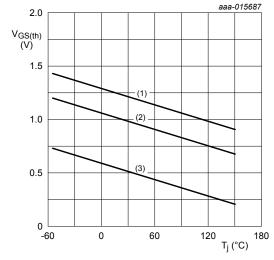


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

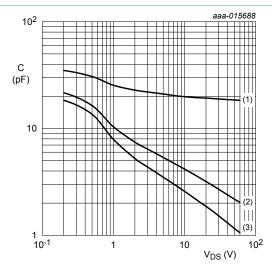
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3)  $C_{rss}$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 55 V, N-channel Trench MOSFET

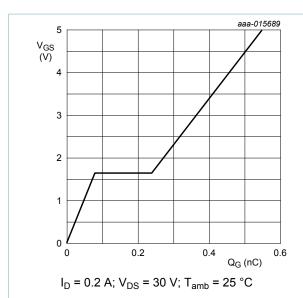


Fig. 14. Gate-source voltage as a function of gate charge; typical values

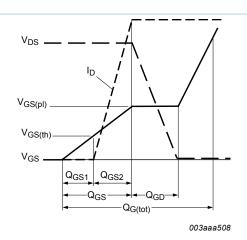
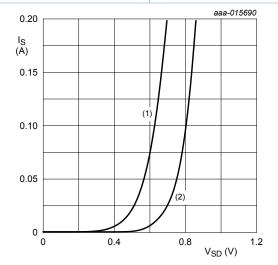


Fig. 15. MOSFET transistor: Gate charge waveform definitions



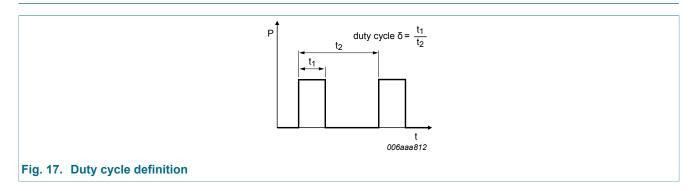
 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 16. Source current as a function of source-drain voltage; typical values

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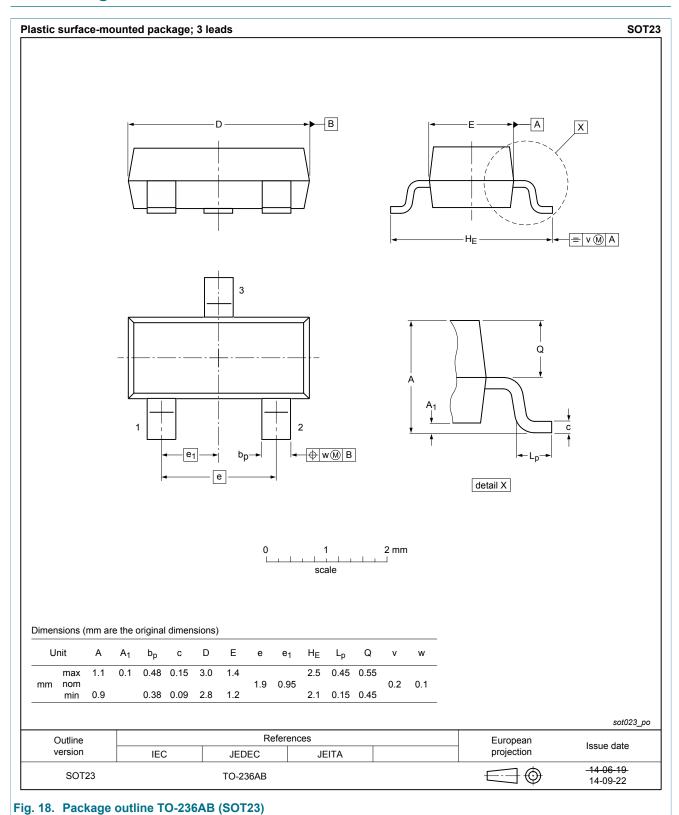
## 11. Test information



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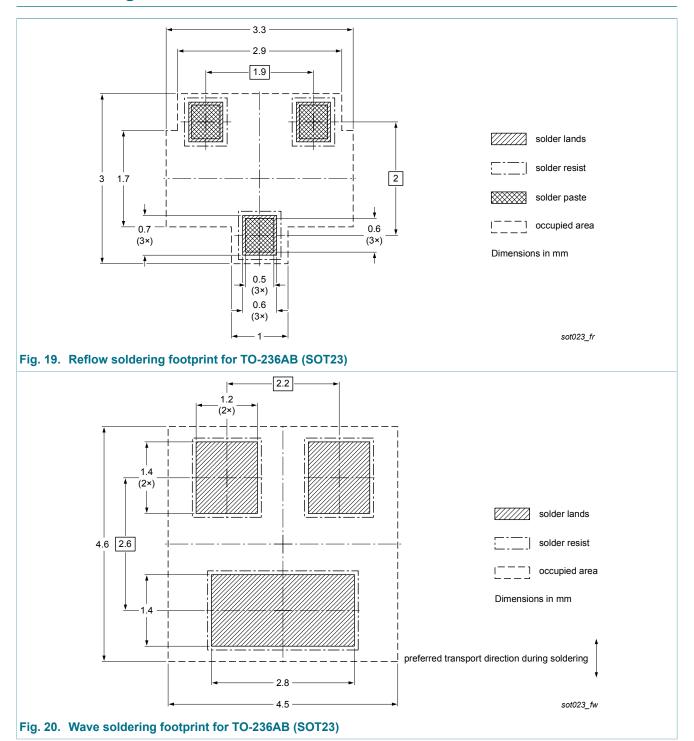
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## 12. Package outline



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### 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSH111BK v.1	20141126	Product data sheet	-	-

#### 55 V, N-channel Trench MOSFET

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#### 15.1 Data sheet status

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